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therebetween and extending in an opposite direction, and

said copper fuse section formed on said first film section of said dielectric film, an end of said copper fuse section being directly connected to said first wiring line by a first section of said first wiring line, which penetrates a portion of said second film section, and another end of said copper fuse section being directly connected to said second wiring line by a second section of said second wiring line, which penetrates a portion of said second film section; and

an opening formed in said third and second film sections of said dielectric film and between said first and second wiring lines, wherein sidewalls of said opening are formed only from said third and second film sections and provide access to said laser beam to oxidize said copper fuse section in said oxidizing environment.

20. (Twice Amended) A semiconductor device that includes a copper fuse, comprising:

a dielectric film including a first film section formed over a substrate, a second film section formed on said first film section, and a third film section formed on said second film section;

a first wiring line and a second wiring line, each of said first wiring line and said second wiring line being formed on said second film section of said dielectric film;

said copper fuse formed on said first film section of said dielectric film, an end of said copper fuse being directly connected to said first wiring line by a first section of said first wiring line, which penetrates a portion of said second film section, and another end of said copper fuse being directly connected to said second wiring line by a second section of said second wiring line, which penetrates a portion of said second film section, and said copper fuse being programmed to a high resistance state by oxidation; and

an opening formed in said third and second film sections of said dielectric film and between said first wiring line and said second wiring line,

wherein sidewalls of said opening are only formed only from said third

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